

SEMICONDUCTOR DEVICE WITH SILICIDE SOURCE/DRAIN AND HIGH-K DIELECTRIC

ABSTRACT OF THE DISCLOSURE

A semiconductor device and method of manufacture. The semiconductor device having a silicide source and a silicide drain; a semiconductor body disposed between the source and the drain; a gate electrode disposed over the body and defining a channel interposed between the source and the drain; and a gate dielectric made from a high-K material and separating the gate electrode and the body.

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